

SHANGHAI SUNRISE ELECTRONICS CO., LTD.

ES1A THRU ES1G

SURFACE MOUNT SUPER FAST SWITCHING RECTIFIER

TECHNICAL SPECIFICATION

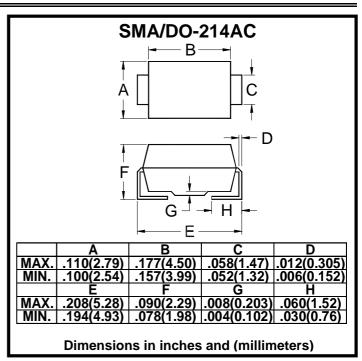
VOLTAGE: 50 TO 400V CURRENT: 1.0A

FEATURES

- Ideal for surface mount pick and place application
- Low profile package
- Built-in strain relief
- High surge capability
- Glass passivated chip
- Super fast recovery for high efficiency
- High temperature soldering guaranteed: 260°C/10sec/at terminal

MECHANICAL DATA

- Terminal: Plated leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	ES1A	ES1B	ES1C	ES1D	ES1E	ES1G	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	V
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	V
Maximum Average Forward Rectified Current $(T_L=110^{\circ}C)$	I _{F(AV)}	1.0						Α
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	30						Α
Maximum Instantaneous Forward Voltage (at rated forward current)	V_{F}	0.95 1.25					V	
Maximum DC Reverse Current $T_a=25^{\circ}C$ (at rated DC blocking voltage) $T_a=100^{\circ}C$	ln.	5.0 200						μA μA
Maximum Reverse Recovery Time (Note 1)	trr	35						nS
Typical Junction Capacitance (Note 2)	C_J	10						pF
Typical Thermal Resistance (Note 3)	R _θ (ja)	40						°C/W
Storage and Operation Junction Temperature	T_{STG},T_{J}	-50 to +150						°C

- Note:
- 1.Reverse recovery condition I_F=0.5A, I_R=1.0A,Irr=0.25A.
- 2.Measured at 1.0 MHz and applied voltage of 4.0V_{dc}
- 3. Thermal resistance from junction to terminal mounted on 5×5mm copper pad area